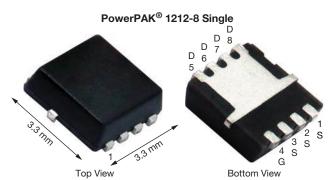


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Vishay Siliconix

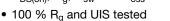
N-Channel 100 V (D-S) MOSFET



PRODUCT SUMMARY				
V _{DS} (V)	100			
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.057			
Q _g typ. (nC)	8.4			
I _D (A)	15.1 ^a			
Configuration	Single			

FEATURES

 \bullet ThunderFET technology optimizes balance of $R_{DS(\text{on})},\,Q_g,\,Q_{sw}$ and Q_{oss}



 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

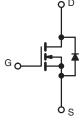


ROHS

HALOGEN FREE

APPLICATIONS

- Fixed telecom
- DC/DC converter
- Primary and secondary side switch
- LED lighting



N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	Si7322ADN-T1-GE3

ABSOLUTE MAXIMUM RATING	iS (T _A = 25 °C, u	ınless otherw	vise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	100	V	
Gate-source voltage		V _{GS}	± 20	V	
	T _C = 25 °C		15.1 ^a		
Continuous dusin surrent (T. 150 °C)	T _C = 70 °C	1 , [12.1		
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	ID	5.4 ^{b, c}		
	T _A = 70 °C	1	4.3 b, c	^	
Pulsed drain current (t = 100 μs)		I _{DM}	20	Α	
	T _C = 25 °C		21.7		
Continuous source-drain diode current	T _A = 25 °C	ls l	2.7 ^{b, c}		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	6		
Single pulse avalanche energy	L = U. I MIH	E _{AS}	1.8	mJ	
	T _C = 25 °C		26		
Maximum navver dissination	T _C = 70 °C	1 , [16.7	W	
Maximum power dissipation	T _A = 25 °C	P _D	3.3 b, c	VV	
	T _A = 70 °C	1 [2.1 ^{b, c}		
Operating junction and storage temperature range		T _J , T _{stq}	-55 to +150	°C	
Soldering recommendations (peak temperature) c			260	-0	

THERMAL RESISTANCE RATING	S				
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^b	t ≤ 10 s	R _{thJA}	31	38	°C/W
Maximum junction-to-case (drain)	Steady state	R _{thJC}	4	4.8	C/VV

Notes

- a. $T_C = 25 \,^{\circ}C$
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 10 s
- 6. 1 10 3 See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 81 °C/W



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				•		•
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		55	-	mV/°C
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-6	-	IIIV/ C
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	-	4	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	100	nA
Zove gets valtege drain surrent		V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V, T _J = 70 °C	-	-	10	μA
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10	-	-	Α
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} =10 V, I _D = 5.5 A	-	0.045	0.057	Ω
Forward transconductance ^a	9 _{fs}	V _{DS} = 5 V, I _D = 5.5 A	-	12	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	360	-	
Output capacitance	C _{oss}	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	130	-	рF
Reverse transfer capacitance	C _{rss}		-	18	-	
Total gate charge	Q_g		-	8.4	13	
Gate-source charge	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5.5 \text{ A}$	-	1.7	-	nC
Gate-drain charge	Q_{gd}			2.6	-	1
Gate resistance	R_g	f = 1 MHz	0.56	2.8	5.6	Ω
Turn-on delay time	t _{d(on)}		-	6	15	
Rise time	t _r	$V_{DD} = 50 \text{ V}, R_L = 10 \Omega, I_D \cong 5 \text{ A},$	-	18	40	1
Turn-off delay time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	_	9	20	ns
Fall time	t _f		_	13	25	1
Drain-Source Body Diode Characteristi	cs					
Continuous source-drain diode current	IS	T _C = 25 °C	-	-	21.7	
Pulse diode forward current	I _{SM}		-	-	20	A
Body diode voltage	V_{SD}	I _S = 5 A, V _{GS} = 0 V	-	0.85	1.2	V
Body diode reverse recovery time	t _{rr}		-	32	60	ns
Body diode reverse recovery charge	Q _{rr}	L EA dI/d+ 100 A/ T 05 00	-	32	60	nC
Reverse recovery fall time	t _a	$I_F = 5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$	-	23	-	
Reverse recovery rise time	t _b		-	9	-	ns

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



0.08

0.06

0.04

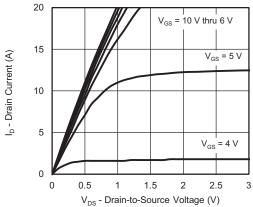
0.02

0

0

R_{DS(on)} - On-Resistance (Ω)

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Output Characteristics

V_{GS} = 10 V



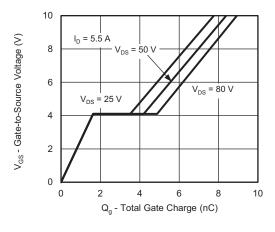
20

 ${\rm I_D}$ - Drain Current (A) ${\rm \bf On\text{-}Resistance} \ {\rm \bf vs.} \ {\rm \bf Drain} \ {\rm \bf Current} \ {\rm \bf and} \ {\rm \bf Gate} \ {\rm \bf Voltage}$

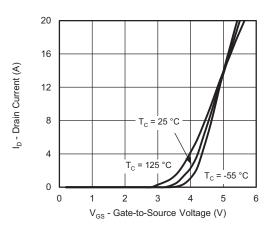
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15

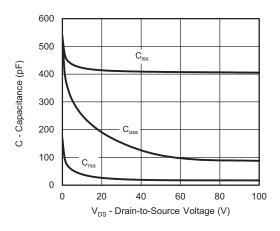
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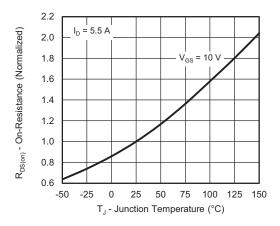
Gate Charge



Transfer Characteristics



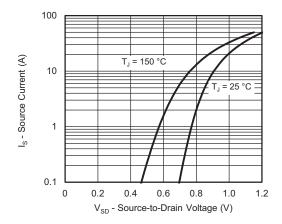
Capacitance



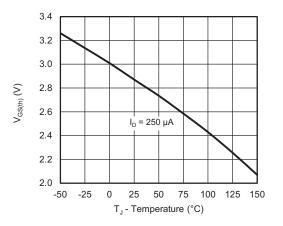
On-Resistance vs. Junction Temperature



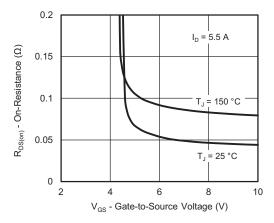
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



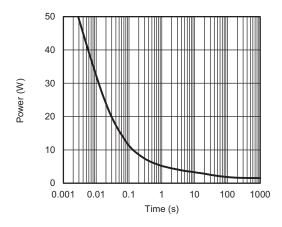
Source-Drain Diode Forward Voltage



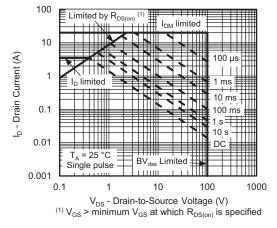
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

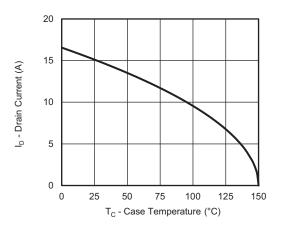


Single Pulse Power, Junction-to-Ambient

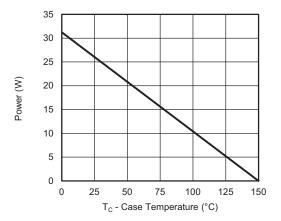


Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating a

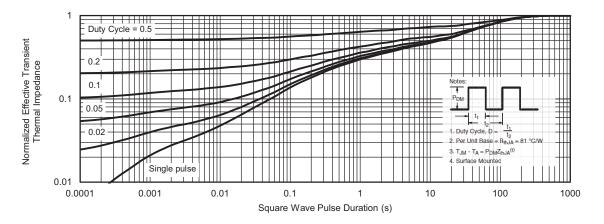


Power, Junction-to-Case

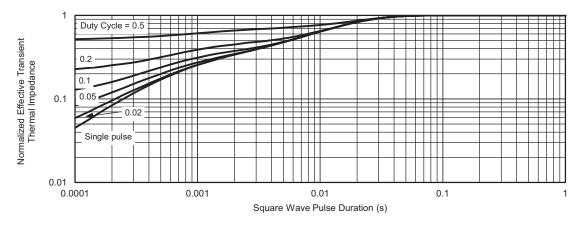
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

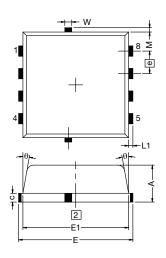


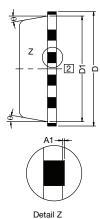
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75590.



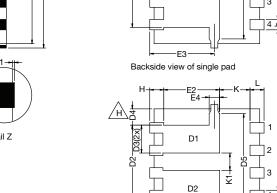
PowerPAK® 1212-8, (Single / Dual)





Notes

- 1. Inch will govern
- 2 Dimensions exclusive of mold gate burrs 3. Dimensions exclusive of mold flash and cutting burrs



Backside view of dual pad

DIM.	MILLIMETERS			INCHES			
DINI.	MIN.	NOM.	MAX.	MIN.	NOM.		
Α	0.97	1.04	1.12	0.038	0.041	0.044	
A1	0.00	-	0.05	0.000	-	0.002	
b	0.23	0.30	0.41	0.009	0.012	0.016	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	3.20	3.30	3.40	0.126	0.130	0.134	
D1	2.95	3.05	3.15	0.116	0.120	0.124	
D2	1.98	2.11	2.24	0.078	0.083	0.088	
D3	0.48	-	0.89	0.019	-	0.035	
D4	0.47 typ.			0.0185 typ			
D5		2.3 typ.		0.090 typ			
Е	3.20	3.30	3.40	0.126	0.130	0.134	
E1	2.95	3.05	3.15	0.116	0.120	0.124	
E2	1.47	1.60	1.73	0.058	0.063	0.068	
E3	1.75	1.85	1.98	0.069	0.073	0.078	
E4		0.034 typ.		0.013 typ.			
е		0.65 BSC			0.026 BSC		
K		0.86 typ.		0.034 typ.			
K1	0.35	-	-	0.014	-	-	
Н	0.30	0.41	0.51	0.012	0.016	0.020	
L	0.30	0.43	0.56	0.012	0.017	0.022	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
М	0.125 typ.			0.005 typ.			

ECN: S16-2667-Rev. M, 09-Jan-17

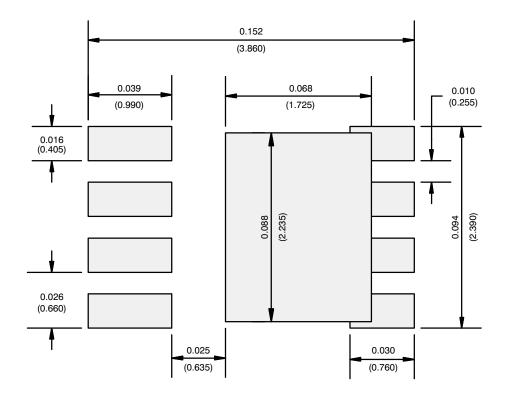
DWG: 5882

Revison: 09-Jan-17

1 Document Number: 71656



RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE

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